

1-Line Uni-directional TVS Diode

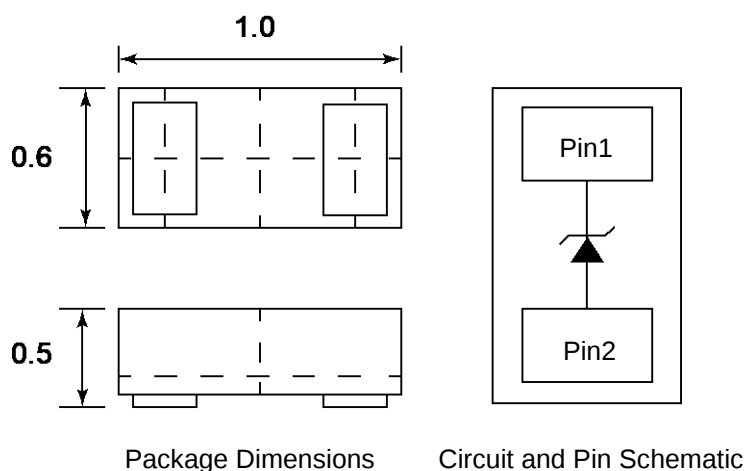
Description

The PESDU3601P1 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU3601P1 complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 25\text{kV}$ contact discharge. It is assembled into an ultra-small DFN1006 lead-free package. The small size and high ESD surge protection make PESDU3601P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one line
- Ultra low leakage: nA level
- Operating voltage: 36V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 25\text{kV}$
 - IEC61000-4-5 (Lightning) 4A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Mechanical Characteristics

- Package: DFN1006-2 (1.0 $\times$ 0.6 $\times$ 0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks, Desktops, Servers
- Portable Instrumentation
- Digital Cameras
- Analog Inputs
- Audio Players
- Keypads, Side Keys, LCD Displays
- Laser Diode Protection

Marking Information



6P. = Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
PESDU3601P1	10000/Tape & Reel	7 inch

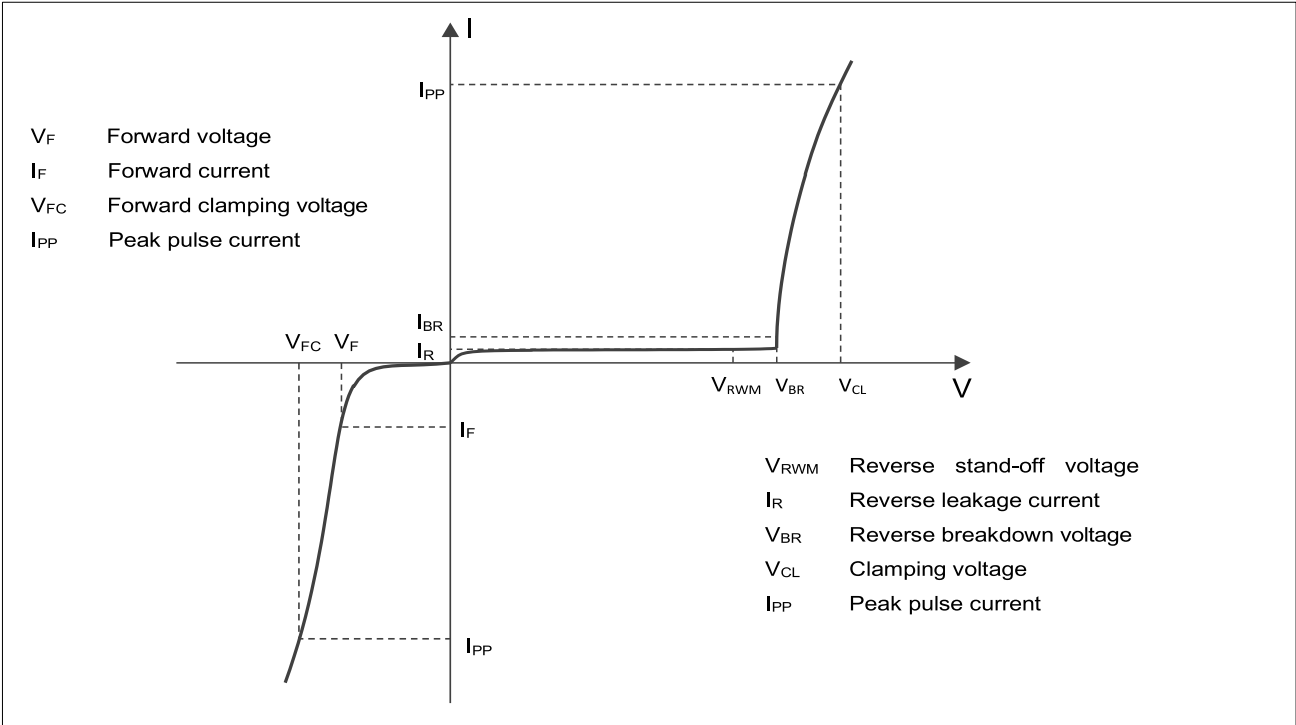
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P _{PK}	300	W
Peak Pulse Current (8/20μs)	I _{PP}	4	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±25	
Lead temperature	T _L	260	°C
Junction Temperature	T _J	125	°C
Operating Temperature Range	T _{OP}	-40 ~ +125	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

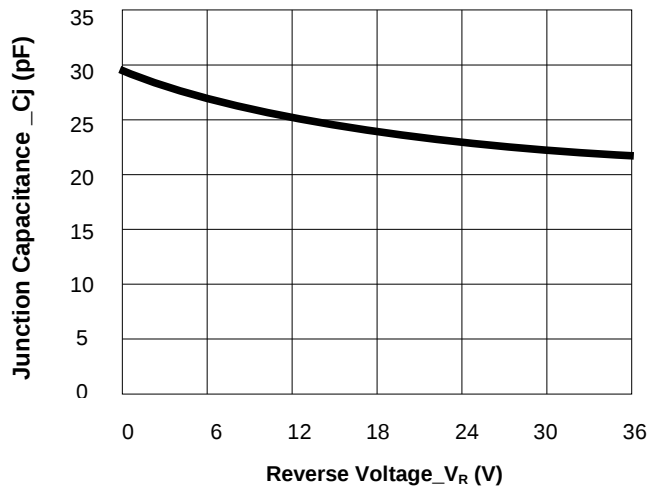
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			36	V	
Breakdown Voltage	V _{BR}	38			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 36V
Clamping Voltage	V _C			50	V	I _{PP} = 1A (8 x 20μs pulse),
Clamping Voltage	V _C			75	V	I _{PP} = 4A (8 x 20μs pulse),
Junction Capacitance	C _J			30	pF	V _R = 0V, f = 1MHz

Electrical characteristics ($T_A = 25^{\circ}\text{C}$, unless otherwise noted)

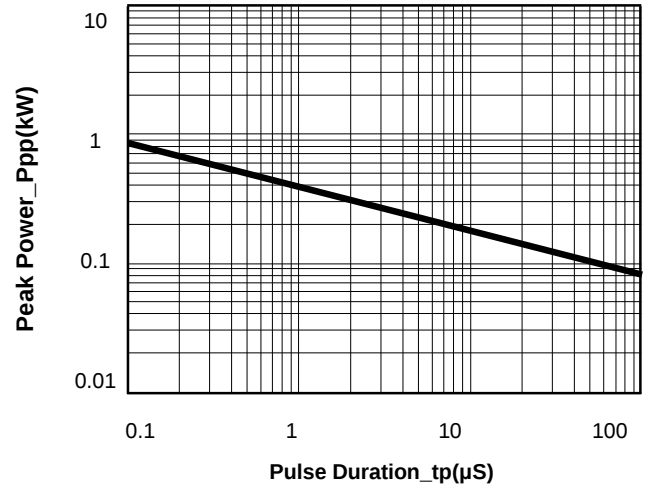


Definitions of electrical characteristics

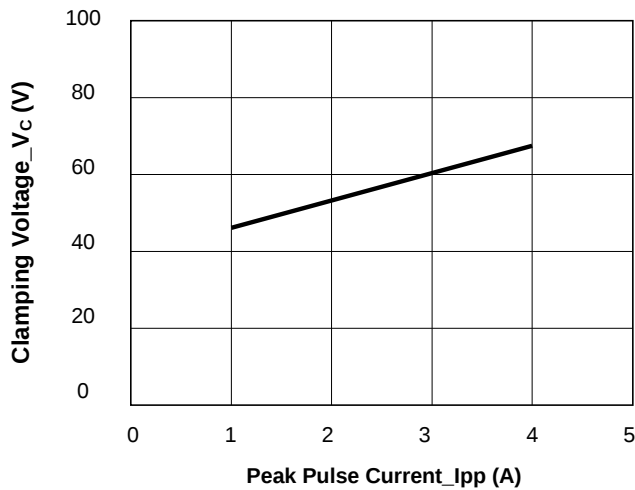
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



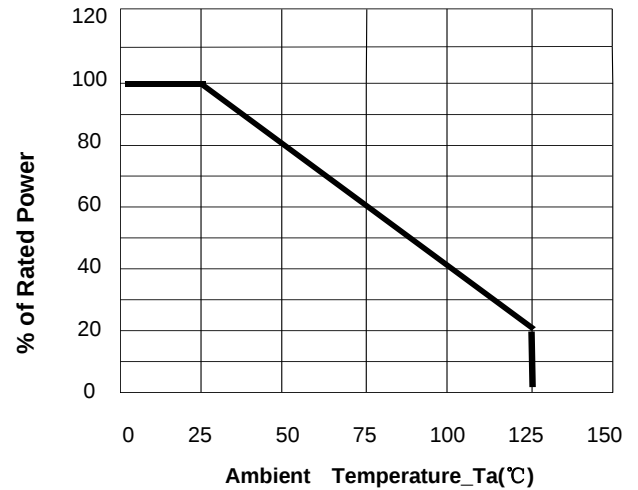
Junction Capacitance vs. Reverse Voltage



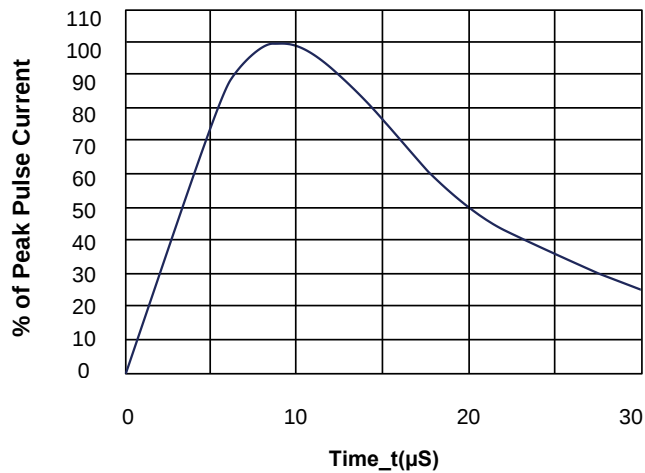
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

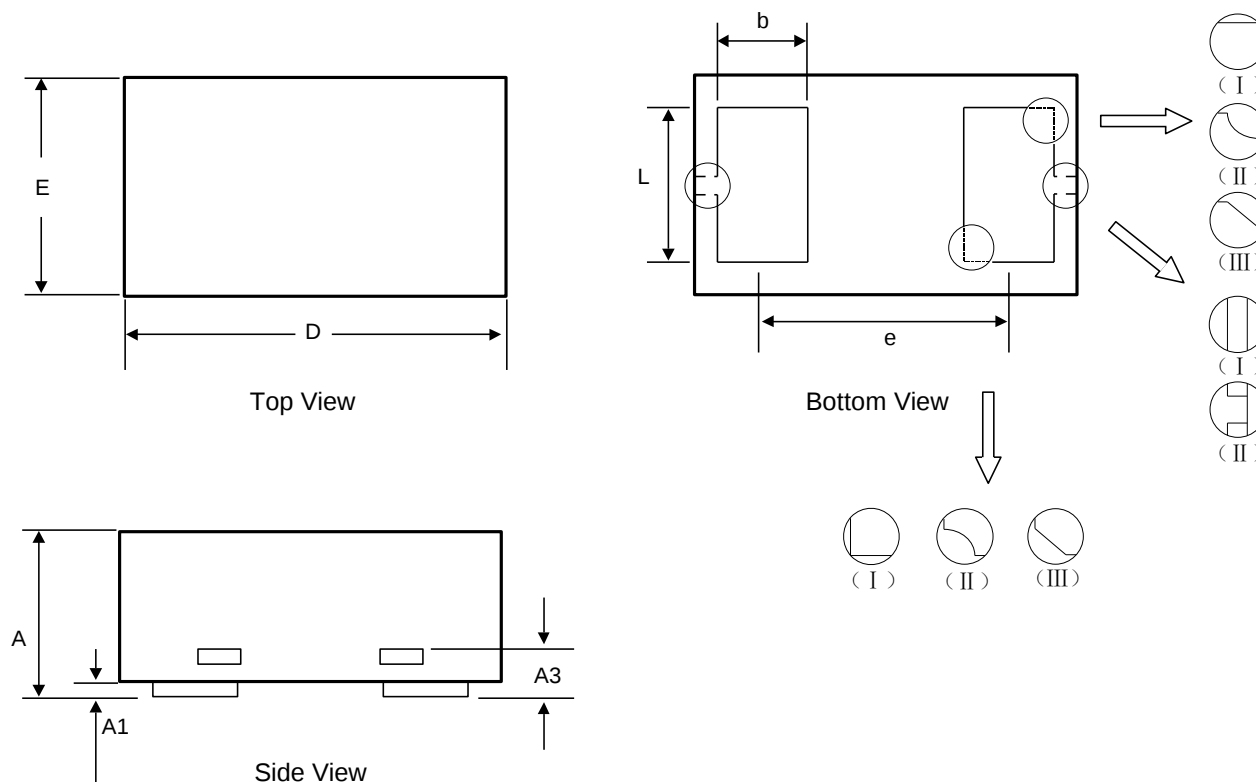


Power Derating Curve



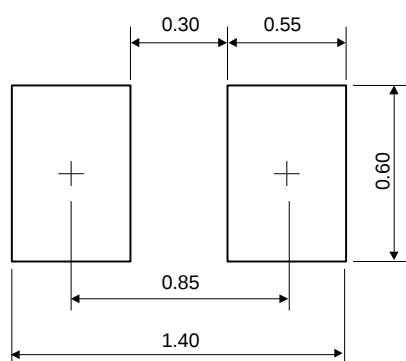
8/20 μs Pulse Waveform

DFN1006-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.550
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)

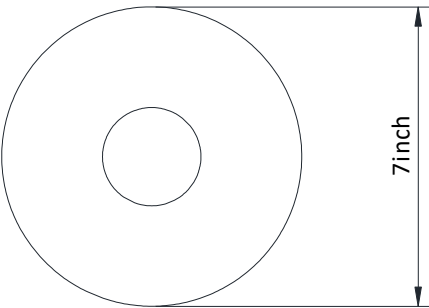


Notes:

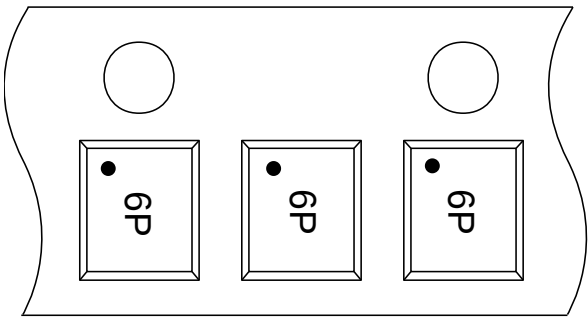
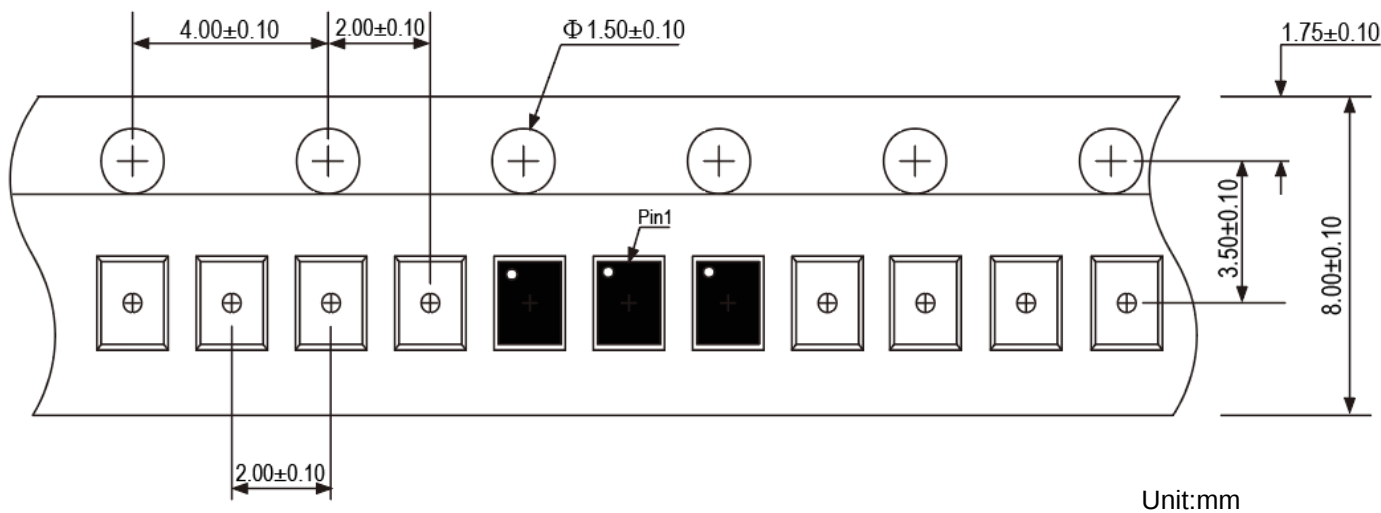
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions



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